Ta =25 unless otherwise specified

Drain-source breakdown voltage	V_{GS} = 0V, I_D =-250μA		-50			
Zero gate voltage drain current	V_{DS} =-50V,V_{GS} = 0V				-15	
	V_{DS} =-25V,V_{GS} = 0V				-0.1	
Gate-body leakage current	V_{GS} =±20V, V_{DS} = 0V				±5	
Gate threshold voltage (note 3)	V_{DS} =V_{GS}, I_D =-250μA		-0.9	-1.6	-2	
Drain-source on-resistance (note 3)	V_{GS} =-5V, I_D =-0.1A			5.8	10	
	V_{GS} =-10V, I_D =-0.1A			4.5	8	
Forward transconductance (note 1)	V_{DS}=-25V; I_D=-100mA		50			
Input capacitance	V_{DS} =5V V_{GS} =0V f =1MHz			30		
Output capacitance				10		
Reverse transfer capacitance				5		
Turn-on delay time	V_{DD}= -15 R_L=50Ω I_D =-2.5A			2.5		
Turn-on rise time				1		
Turn-off delay time				16		
Turn-off fall time				8		
Continuous Current					-0.13	
Pulsed Current					-0.52	
Diode forward voltage (note 3)	I_S=-0.13A, V_{GS} = 0V	SD			-2.2	

1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , t≤10s.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤2%.
4. Guaranteed by design, not subject to producting.

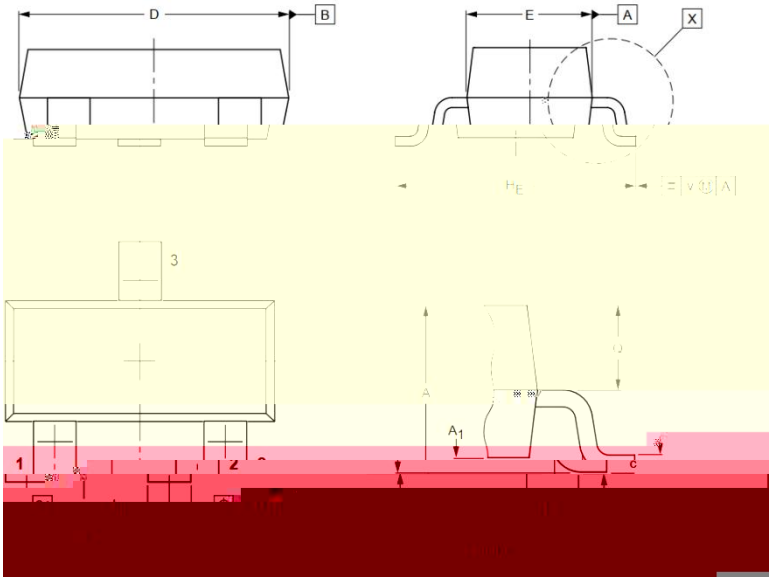


Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel,7"reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

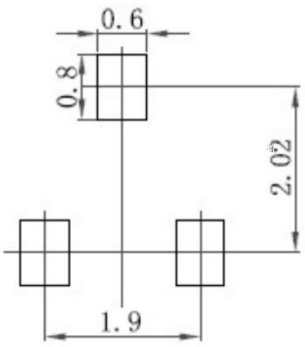
Package Dimensions

SOT-23



Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
e	1.9		75	
e1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



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